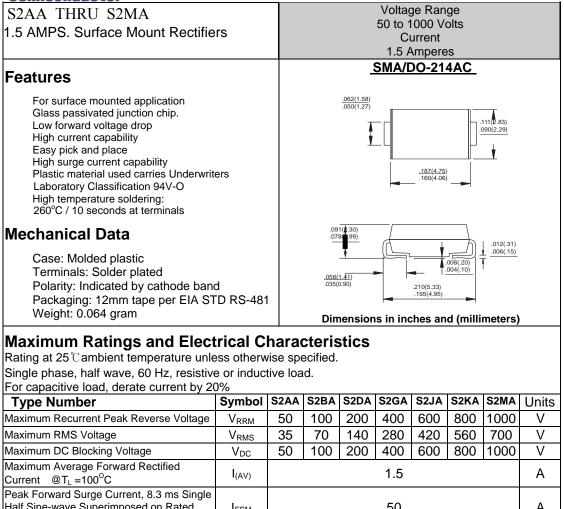
## GMGarboMicro Semiconductor

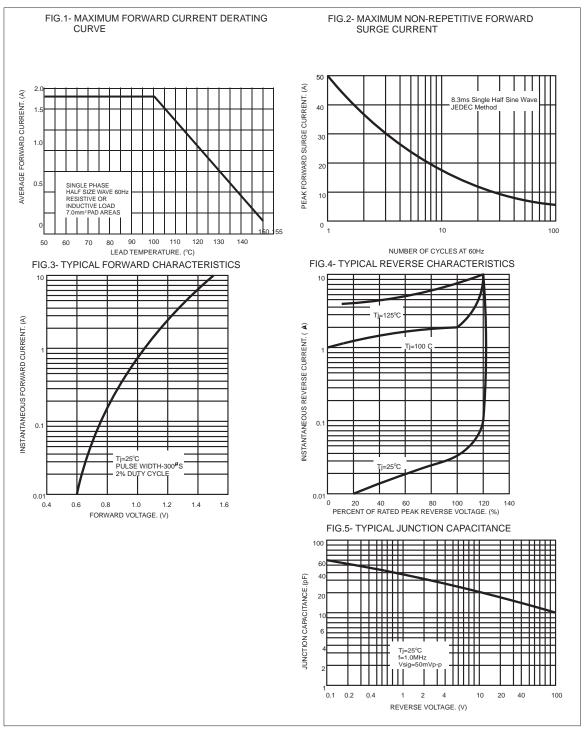


Load (JEDEC method )	IFSM	50	A
Maximum Instantaneous Forward Voltage @ 1.5A	VF	1.1	V
Maximum DC Reverse Current @ $T_A = 25^{\circ}C$ at Rated DC Blocking Voltage @ $T_A = 125^{\circ}C$	I <sub>R</sub>	5.0 125	uA uA
Typical Thermal Resistance (Note 3)	${\sf R}  heta_{\sf JL}$ ${\sf R}  heta_{\sf JA}$	16 53	°C/W
Maximum Reverse Recovery Time ( Note 1 )	Trr	2.0	uS
Typical Junction Capacitance (Note 2)	Cj	30	pF
Operating Temperature Range	TJ	-55 to +150	0°C
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	°C

Notes: 1. Reverse Recovery Test Conditions: IF=0.5A, IR=1.0A, IRR=0.25A

2. Measured at 1 MHz and Applied V<sub>R</sub>=4.0 Volts

3. Measured on P.C. Board with 0.2 x 0.2" (5.0 x 5.0mm) Copper Pad Areas.



## RATINGS AND CHARACTERISTIC CURVES (S2AA THRU S2MA)

Http://www.gmsemi.com